Oliver Brandt

List of Publications by Year
in descending order

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388 papers	13,079 citations	26567 56 h-index	37111 96 g-index
401 all docs	401 docs citations	401 times ranked	7461 citing authors

#	Article	IF	Citations
1	Cross-sectional shape evolution of GaN nanowires during molecular beam epitaxy growth on Si(111). Nanoscale Advances, 2022, 4, 562-572.	2.2	2
2	Carrier Diffusion in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math> : A Cathodoluminescence Study. II. Ambipolar versus Exciton Diffusion. Physical Review Applied, 2022, 17, .	1.5	6
3	Carrier Diffusion in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math> : A Cathodoluminescence Study. I. Temperature-Dependent Generation Volume. Physical Review Applied, 2022, 17, .	1.5	6
4	Carrier Diffusion in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math> : A Cathodoluminescence Study. III. Nature of Nonradiative Recombination at Threading Dislocations. Physical Review Applied, 2022, 17, .	1.5	9
5	Interface Recombination in Ga- and N-Polar GaN/(Al,Ga)N Quantum Wells Grown by Molecular Beam Epitaxy. Physical Review Applied, 2022, 17, .	1.5	2
6	Enhanced Radiative Efficiency in GaN Nanowires Grown on Sputtered TiN_x: Effects of Surface Electric Fields. ACS Photonics, 2021, 8, 1718-1725.	3.2	6
7	External Control of GaN Band Bending Using Phosphonate Self-Assembled Monolayers. ACS Applied Materials & Interfaces, 2021, 13, 4626-4635.	4.0	6
8	Drastic Effect of Sequential Deposition Resulting from Flux Directionality on the Luminescence Efficiency of Nanowire Shells. ACS Applied Materials & Interfaces, 2021, 13, 50220-50227.	4.0	1
9	Drastically enhanced cation incorporation in the epitaxy of oxides due to formation and evaporation of suboxides from elemental sources. APL Materials, 2021, 9, .	2.2	10
10	Coaxial GaAs/(In,Ga)As Dot-in-a-Well Nanowire Heterostructures for Electrically Driven Infrared Light Generation on Si in the Telecommunication O Band. ACS Applied Nano Materials, 2020, 3, 165-174.	2.4	14
11	Selfâ€Assembly of Wellâ€Separated AlN Nanowires Directly on Sputtered Metallic TiN Films. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900615.	1.2	5
12	Radius-dependent homogeneous strain in uncoalesced GaN nanowires. Acta Materialia, 2020, 195, 87-97.	3.8	9
13	Absence of Quantum-Confined Stark Effect in GaN Quantum Disks Embedded in (Al,Ga)N Nanowires Grown by Molecular Beam Epitaxy. Nano Letters, 2019, 19, 5938-5948.	4.5	7
14	Electroluminescence and currentâ€“voltage measurements of single-(In,Ga)N/GaN-nanowire light-emitting diodes in a nanowire ensemble. Beilstein Journal of Nanotechnology, 2019, 10, 1177-1187.	1.5	8
15	Semicoherent growth of single-crystal Î²-In₂S₃ layers on InP(111) and InAs(111). CrystEngComm, 2019, 21, 5818-5823.	1.3	2
16	Top-down fabrication of ordered arrays of GaN nanowires by selective area sublimation. Nanoscale Advances, 2019, 1, 1893-1900.	2.2	23
17	Interfacial reactions during the molecular beam epitaxy of GaN nanowires on Ti/Al₂O₃. Nanotechnology, 2019, 30, 114001.	1.3	13
18	Electron spin dynamics in mesoscopic GaN nanowires. Applied Physics Letters, 2019, 114, 092406.	1.5	8

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19	Impact of Outer Shell Structure and Localization Effects on Charge Carrier Dynamics in GaAs/(In,Ga)As Nanowire Coreâ€“Shell Quantum Wells. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800527.	1.2	7
20	Optical properties of GaN nanowires grown on chemical vapor deposited-graphene. Nanotechnology, 2019, 30, 214005.	1.3	11
21	Determination of the Carrier Diffusion Length in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math>from Cathodoluminescence Maps Around Threading Dislocations: Fallacies and Opportunities. Physical Review Applied, 2019, 12, .	1.5	16
22	Excitonic Aharonovâ€“Bohm Oscillations in Coreâ€“Shell Nanowires. Advanced Materials, 2019, 31, 1805645.	11.1	14
23	Crystal-Phase Quantum Wires: One-Dimensional Heterostructures with Atomically Flat Interfaces. Nano Letters, 2018, 18, 247-254.	4.5	7
24	Luminescent N-polar (In,Ga)N/GaN quantum wells achieved by plasma-assisted molecular beam epitaxy at temperatures exceeding 700â€‰Â°C. Applied Physics Letters, 2018, 112, .	1.5	13
25	Electronic properties of wurtzite GaAs: A correlated structural, optical, and theoretical analysis of the same polytypic GaAs nanowire. Nano Research, 2018, 11, 4708-4721.	5.8	29
26	Piezoelectric field, exciton lifetime, and cathodoluminescence intensity at threading dislocations in GaN{0001}. Applied Physics Letters, 2018, 112, .	1.5	12
27	Nanowires Bending over Backward from Strain Partitioning in Asymmetric Coreâ€“Shell Heterostructures. Nano Letters, 2018, 18, 2343-2350.	4.5	35
28	Self-assembled formation of long, thin, and uncoalesced GaN nanowires on crystalline TiN films. Nano Research, 2018, 11, 565-576.	5.8	31
29	Monitoring the formation of GaN nanowires in molecular beam epitaxy by polarization-resolved optical reflectometry. CrystEngComm, 2018, 20, 3202-3206.	1.3	8
30	Plasma-assisted molecular beam epitaxy of GaN nanowires on epitaxial single-layer graphene. , 2018, , .		1
31	Influence of strain relaxation in axial ${mathrm{In}}_{x}{mathrm{Ga}}_{1-x}{m{N}}/mathrm{GaN}$ nanowire heterostructures on their electronic properties. Nanotechnology, 2017, 28, 215204.	1.3	2
32	In/GaN(0001)-(3Ã—3)R30Â° adsorbate structure as a template for embedded (In, Ga)N/GaN monolayers and short-period superlattices. Applied Physics Letters, 2017, 110, .	1.5	21
33	Polarity-Induced Selective Area Epitaxy of GaN Nanowires. Nano Letters, 2017, 17, 63-70.	4.5	18
34	Luminous Efficiency of Ordered Arrays of GaN Nanowires with Subwavelength Diameters. ACS Photonics, 2017, 4, 52-62.	3.2	21
35	Quantum Dot Self-Assembly Driven by a Surfactant-Induced Morphological Instability. Physical Review Letters, 2017, 119, 086101.	2.9	18
36	Dislocation contrast in cathodoluminescence and electron-beam induced current maps on GaN(0â€‰0â€‰0â€‰1). Journal Physics D: Applied Physics, 2017, 50, 405101.	1.3	31

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37	Efficient methodology to correlate structural with optical properties of GaAs nanowires based on scanning electron microscopy. Nanotechnology, 2017, 28, 415703.	1.3	7
38	Ga-Polar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mo stretchy="false">(</mml:mo><mml:mi>In</mml:mi><mml:mo>,</mml:mo><mml:mi>Ga</mml:mi><mml:mo) Tj ETQq0 0 0 rgBT /Overlo mathvariant="normal">N</mml:mi><mml:mo>/</mml:mo><mml:mi>GaN</mml:mi></mml:mrow></mml:math> Quantum Wells Versus N-Polar (In,Ga)N Quantum Disks in GaN Nanowires: A Comparative Analysis of C	1.5	9
39	Fine structure of excitons in InAs quantum dots on GaAs(110) planar layers and nanowire facets. Physical Review B, 2017, 96, .	1.1	3
40	Modeling the electronic properties of GaAs polytype nanostructures: Impact of strain on the conduction band character. Physical Review B, 2017, 95, .	1.1	14
41	Metal-Exchange Catalysis in the Growth of Sesquioxides: Towards Heterostructures of Transparent Oxide Semiconductors. Physical Review Letters, 2017, 119, 196001.	2.9	68
42	Self-Assembly of InAs Nanostructures on the Sidewalls of GaAs Nanowires Directed by a Bi Surfactant. Nano Letters, 2017, 17, 4255-4260.	4.5	19
43	Molecular Beam Epitaxy of GaN Nanowires on Epitaxial Graphene. Nano Letters, 2017, 17, 5213-5221.	4.5	72
44	Effect of surface roughness, chemical composition, and native oxide crystallinity on the orientation of self-assembled GaN nanowires on Ti foils. Nanotechnology, 2017, 28, 425602.	1.3	20
45	Broad Band Light Absorption and High Photocurrent of (In,Ga)N Nanowire Photoanodes Resulting from a Radial Stark Effect. ACS Applied Materials & Interfaces, 2016, 8, 34490-34496.	4.0	5
46	Electron spin dynamics in cubic GaN. Physical Review B, 2016, 94, .	1.1	9
47	Counterintuitive strain distribution in axial (In,Ga)N/GaN nanowires. Applied Physics Letters, 2016, 108, .	1.5	14
48	Molecular beam epitaxy of single crystalline GaN nanowires on a flexible Ti foil. Applied Physics Letters, 2016, 108, .	1.5	79
49	Polarity in GaN and ZnO: Theory, measurement, growth, and devices. Applied Physics Reviews, 2016, 3, .	5.5	105
50	Exciton recombination at crystal-phase quantum rings in GaAs/InxGa1â^'xAs core/multishell nanowires. Applied Physics Letters, 2016, 109, .	1.5	10
51	Individual electron and hole localization in submonolayer InN quantum sheets embedded in GaN. Applied Physics Letters, 2016, 109, 042104.	1.5	6
52	Nucleation, Growth, and Bundling of GaN Nanowires in Molecular Beam Epitaxy: Disentangling the Origin of Nanowire Coalescence. Nano Letters, 2016, 16, 3717-3725.	4.5	49
53	(Al,Ga)O_x Microwire Ensembles on Si Exhibiting Luminescence over the Entire Visible Wavelength Range. Advanced Optical Materials, 2016, 4, 2017-2020.	3.6	2
54	Comparison of the Luminous Efficiencies of Ga- and N-Polar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>In</mml:mi></mml:mrow><mml:mrow><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:mo mathvariant="normal">N</mml:mi><mml:mo stretchy="false">/</mml:mo><mml:msub><mml:mrow><mml:mi>In</mml:mi></mml:mrow><mml:mrow><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:mo>. Physical Review Applied, 2016, 6, .	1.5	16

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55	Quenching of the luminescence intensity of GaN nanowires under electron beam exposure: impact of C adsorption on the exciton lifetime. Nanotechnology, 2016, 27, 455706.	1.3	7
56	Crystal-phase quantum dots in GaN quantum wires. Physical Review B, 2016, 93, .	1.1	5
57	Nature of excitons bound to inversion domain boundaries: Origin of the 3.45-eV luminescence lines in spontaneously formed GaN nanowires on Si(111). Physical Review B, 2016, 94, .	1.1	10
58	Simulations of the electronic properties of GaAs polytype superlattices. , 2016, , .		0
59	Exciton dynamics in GaAs/(Al,Ga)As core-shell nanowires with shell quantum dots. Physical Review B, 2016, 94, .	1.1	10
60	Elastic versus Plastic Strain Relaxation in Coalesced GaN Nanowires: An X-Ray Diffraction Study. Physical Review Applied, 2016, 6, .	1.5	12
61	Self-assembled growth of GaN nanowires on amorphous AlxOy: from nucleation to the formation of dense nanowire ensembles. Nanotechnology, 2016, 27, 325601.	1.3	23
62	Radial Stark Effect in (In,Ga)N Nanowires. Nano Letters, 2016, 16, 917-925.	4.5	21
63	Impact of substrate nitridation on the growth of InN on In 2 O 3 (111) by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2016, 369, 159-162.	3.1	5
64	Piezoelectric potential in axial (In,Ga)N/GaN nanowire heterostructures. Nanotechnology, 2016, 27, 165201.	1.3	8
65	Observation of Dielectrically Confined Excitons in Ultrathin GaN Nanowires up to Room Temperature. Nano Letters, 2016, 16, 973-980.	4.5	40
66	In-plane sixfold symmetry for<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>Î±</mml:mi></mml:math>-Fe(110) on GaN{0001}: Measurement of the cubic anisotropy constant<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>K</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:m Fe. Physical Review B, 2015, 92, .	1.1	3
67	Quantitative evaluation of the broadening of x-ray diffraction, Raman, and photoluminescence lines by dislocation-induced strain in heteroepitaxial GaN films. Journal Physics D: Applied Physics, 2015, 48, 385105.	1.3	20
68	Epitaxial Growth of GaN Nanowires with High Structural Perfection on a Metallic TiN Film. Nano Letters, 2015, 15, 3743-3747.	4.5	69
69	Impact of Random Dopant Fluctuations on the Electronic Properties of In_xGa_{1â€“x}N/GaN Axial Nanowire Heterostructures. Nano Letters, 2015, 15, 4289-4294.	4.5	11
70	Improved control over spontaneously formed GaN nanowires in molecular beam epitaxy using a two-step growth process. Nanotechnology, 2015, 26, 445604.	1.3	15
71	Stochastic model for the fluctuation-limited reactionâ€“diffusion kinetics in inhomogeneous media based on the nonlinear Smoluchowski equations. Journal of Mathematical Chemistry, 2015, 53, 651-669.	0.7	24
72	Monitoring the Formation of Nanowires by Line-of-Sight Quadrupole Mass Spectrometry: A Comprehensive Description of the Temporal Evolution of GaN Nanowire Ensembles. Nano Letters, 2015, 15, 1930-1937.	4.5	53

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73	Electronic properties of axial In $$_x$$ x Ga $$_{1-x}$$ 1 - x N insertions in GaN nanowires. Journal of Computational Electronics, 2015, 14, 464-468.	1.3	4
74	Compatibility of the selective area growth of GaN nanowires on AlN-buffered Si substrates with the operation of light emitting diodes. Nanotechnology, 2015, 26, 085605.	1.3	27
75	Importance of the dielectric contrast for the polarization of excitonic transitions in single GaN nanowires. New Journal of Physics, 2015, 17, 033040.	1.2	16
76	Non-destructive assessment of the polarity of GaN nanowire ensembles using low-energy electron diffraction and x-ray photoelectron diffraction. Applied Physics Letters, 2015, 106, .	1.5	23
77	High-Temperature Growth of GaN Nanowires by Molecular Beam Epitaxy: Toward the Material Quality of Bulk GaN. Crystal Growth and Design, 2015, 15, 4104-4109.	1.4	34
78	Integration of GaN Crystals on Micropatterned Si(0 0 1) Substrates by Plasma-Assisted Molecular Beam Epitaxy. Crystal Growth and Design, 2015, 15, 4886-4892.	1.4	10
79	Atomistic description of wave function localization effects in In_xGa_{1-x}N alloys and quantum wells. Proceedings of SPIE, 2015, , .	0.8	8
80	Localization and defects in axial (In,Ga)N/GaN nanowire heterostructures investigated by spatially resolved luminescence spectroscopy. Journal Physics D: Applied Physics, 2014, 47, 394010.	1.3	12
81	Stacking faults as quantum wells in nanowires: Density of states, oscillator strength, and radiative efficiency. Physical Review B, 2014, 90, .	1.1	42
82	Origin of the nonradiative decay of bound excitons in GaN nanowires. Physical Review B, 2014, 90, .	1.1	32
83	Sub-meV linewidth in GaN nanowire ensembles: Absence of surface excitons due to the field ionization of donors. Physical Review B, 2014, 90, .	1.1	26
84	Minimizing the influence of surface potentials in axial In<inf>x</inf>Ga<inf>1−x</inf>N/GaN nanowire heterostructures by reducing their diameter. , 2014, , .		0
85	Uniaxial magnetic anisotropy in epitaxial Î±â€Fe() films. Annalen Der Physik, 2014, 526, L1.	0.9	6
86	Correlation between the structural and optical properties of spontaneously formed GaN nanowires: a quantitative evaluation of the impact of nanowire coalescence. Nanotechnology, 2014, 25, 455702.	1.3	44
87	Radiative and nonradiative decay of excitons in GaN nanowires. Proceedings of SPIE, 2014, , .	0.8	3
88	Statistical Analysis of the Shape of One-Dimensional Nanostructures: Determining the Coalescence Degree of Spontaneously Formed GaN Nanowires. Crystal Growth and Design, 2014, 14, 2246-2253.	1.4	44
89	Luminescence associated with stacking faults in GaN. Journal Physics D: Applied Physics, 2014, 47, 423001.	1.3	92
90	Understanding peculiarities in the optoelectronic characteristics of light emitting diodes based on (In,Ga)N/GaN nanowires. Applied Physics Letters, 2014, 105, .	1.5	17

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91	Minimizing the impact of surface potentials in axial InxGa1â^'xN/GaN nanowire heterostructures by reducing their diameter. Journal Physics D: Applied Physics, 2014, 47, 394007.	1.3	6
92	Analysis of reciprocal space maps of GaN(0001) films grown by molecular beam epitaxy. Journal of Applied Crystallography, 2014, 47, 256-263.	1.9	17
93	All-electrical spin injection and detection in the Co2FeSi/GaAs hybrid system in the local and non-local configuration. Applied Physics Letters, 2013, 103, .	1.5	67
94	Quenching of the E2 phonon line in the Raman spectra of wurtzite GaAs nanowires caused by the dielectric polarization contrast. Applied Physics Letters, 2013, 103, 043121.	1.5	8
95	Strain Engineering of Nanowire Multi-Quantum Well Demonstrated by Raman Spectroscopy. Nano Letters, 2013, 13, 4053-4059.	4.5	33
96	Height self-equilibration during the growth of dense nanowire ensembles: Order emerging from disorder. Applied Physics Letters, 2013, 103, .	1.5	44
97	Ultraviolet light-emitting diodes grown by plasma-assisted molecular beam epitaxy on semipolar GaN (202Â¯1) substrates. Applied Physics Letters, 2013, 102, .	1.5	9
98	Observation of the electron-accumulation layer at the surface of InN by cross-sectional micro-Raman spectroscopy. Applied Physics Letters, 2013, 102, .	1.5	5
99	Luminous Efficiency of Axial In_xGa_{1â€“x}N/GaN Nanowire Heterostructures: Interplay of Polarization and Surface Potentials. Nano Letters, 2013, 13, 3298-3304.	4.5	30
100	Self-Regulated Radius of Spontaneously Formed GaN Nanowires in Molecular Beam Epitaxy. Nano Letters, 2013, 13, 3274-3280.	4.5	104
101	Investigation on the origin of luminescence quenching in N-polar (In,Ga)N multiple quantum wells. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	0.6	15
102	Excitation polarization anisotropy of the spontaneous emission from an<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>M</mml:mi></mml:math>-plane GaN film: Competition between hole relaxation and exciton recombination. Physical Review B, 2013, 87, .	1.1	2
103	Coupling of exciton states as the origin of their biexponential decay dynamics in GaN nanowires. Physical Review B, 2013, 88, .	1.1	22
104	Auger recombination as the dominant nonradiative recombination channel in InN. Physical Review B, 2013, 87, .	1.1	14
105	Carrier Transport in GaAs Nanowires Using Surface Acoustic Waves. Materials Research Society Symposia Proceedings, 2012, 1408, 43.	0.1	2
106	Influence of nanowire template morphology on the coalescence overgrowth of GaN nanowires on Si by molecular beam epitaxy. Proceedings of SPIE, 2012, , .	0.8	0
107	Structural properties of InN films grown on O-face ZnO(0001Â¯) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2012, 100, 152105.	1.5	20
108	Growth of wurtzite InN on bulk In2O3(111) wafers. Applied Physics Letters, 2012, 101, .	1.5	16

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109	Effects of Ga on the growth of InN on O-face ZnO(0001Â¯) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2012, 101, 052103.	1.5	2
110	Spontaneous Nucleation and Growth of GaN Nanowires: The Fundamental Role of Crystal Polarity. Nano Letters, 2012, 12, 6119-6125.	4.5	106
111	Time-resolved photoluminescence spectroscopy of individual GaN nanowires. Physical Review B, 2012, 86, .	1.1	26
112	Direct experimental determination of the spontaneous polarization of GaN. Physical Review B, 2012, 86, .	1.1	94
113	Correlation between In content and emission wavelength of In_xGa_{1â^'x}N/GaN nanowire heterostructures. Nanotechnology, 2012, 23, 455203.	1.3	23
114	Acoustically Driven Photon Antibunching in Nanowires. Nano Letters, 2012, 12, 252-258.	4.5	54
115	Luminescence of GaAs nanowires consisting of wurtzite and zinc-blende segments. Physical Review B, 2012, 85, .	1.1	113
116	Inhomogeneous strain in GaN nanowires determined from x-ray diffraction peak profiles. Physical Review B, 2012, 86, .	1.1	28
117	Polarized recombination of acoustically transported carriers in GaAs nanowires. Nanoscale Research Letters, 2012, 7, 247.	3.1	1
118	Current path in light emitting diodes based on nanowire ensembles. Nanotechnology, 2012, 23, 465301.	1.3	50
119	Indium Incorporation in In_xGa_{1â€“x}N/GaN Nanowire Heterostructures Investigated by Line-of-Sight Quadrupole Mass Spectrometry. Crystal Growth and Design, 2012, 12, 5686-5692.	1.4	14
120	Raman spectroscopy as a probe for the coupling of light into ensembles of sub-wavelength-sized nanowires. Applied Physics Letters, 2012, 101, 083104.	1.5	13
121	Raman scattering by wave-vector-dependent coupled plasmon/LO-phonon modes in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>n</mml:mi></mml:math>-type InN. Physical Review B, 2012, 85, .	1.1	9
122	Electrical characterization of all-epitaxial Fe/GaN(0001) Schottky tunnel contacts. Applied Physics Letters, 2012, 101, .	1.5	8
123	GaN/Fe core/shell nanowires for nonvolatile spintronics on Si. Physical Review B, 2011, 83, .	1.1	8
124	Suitability of Au- and Self-Assisted GaAs Nanowires for Optoelectronic Applications. Nano Letters, 2011, 11, 1276-1279.	4.5	180
125	Formation of High-Quality GaN Microcrystals by Pendeoepitaxial Overgrowth of GaN Nanowires on Si(111) by Molecular Beam Epitaxy. Crystal Growth and Design, 2011, 11, 4257-4260.	1.4	30
126	Coexistence of quantum-confined Stark effect and localized states in an (In,Ga)N/GaN nanowire heterostructure. Physical Review B, 2011, 84, .	1.1	42

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127	Nitride nanowire structures for LED applications. Proceedings of SPIE, 2011, , .	0.8	1
128	Monodisperse (In, Ga)N insertions in catalyst-free-grown GaN(0001) nanowires. Nanotechnology, 2011, 22, 469501.	1.3	1
129	Properties of GaN Nanowires Grown by Molecular Beam Epitaxy. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 878-888.	1.9	104
130	Macro- and micro-strain in GaN nanowires on Si(111). Nanotechnology, 2011, 22, 295714.	1.3	61
131	X-ray diffraction profiles from axial nanowire heterostructures. Physical Review B, 2011, 83, .	1.1	8
132	Effect of growth temperature on the structural, morphological and magnetic properties of Fe films on GaN(0001). Journal of Crystal Growth, 2011, 323, 359-362.	0.7	5
133	GaN nanowire templates for the pendeoepitaxial coalescence overgrowth on Si(111) by molecular beam epitaxy. Journal of Crystal Growth, 2011, 323, 418-421.	0.7	21
134	Multi-channel magnetotransport in Co2FeSi/(Al,Ga)As spin-LEDs. Solid State Communications, 2011, 151, 436-439.	0.9	5
135	Monodisperse (In, Ga)N insertions in catalyst-free-grown GaN(0001) nanowires. Nanotechnology, 2011, 22, 365703.	1.3	15
136	Epitaxial Interfaces between Crystallographically Mismatched Materials. Physical Review Letters, 2011, 107, 026102.	2.9	15
137	Disorder-induced reversal of spin polarization in the Heusler alloy Co<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>FeSi. Physical Review B, 2011, 83, .	1.1	38
138	Analyzing the growth of InxGa1âˆ'xN/GaN superlattices in self-induced GaN nanowires by x-ray diffraction. Applied Physics Letters, 2011, 98, 261907.	1.5	18
139	Comparison of the spectral and temporal emission characteristics of homoepitaxial and heteroepitaxial ZnO nanowires. Applied Physics Letters, 2011, 98, 113113.	1.5	13
140	Surface-induced effects in GaN nanowires. Journal of Materials Research, 2011, 26, 2157-2168.	1.2	107
141	Ferromagnetism in lightly Gd doped GaN: The role of defects. Materials Research Society Symposia Proceedings, 2011, 1290, 1.	0.1	2
142	Direct comparison of catalyst-free and catalyst-induced GaN nanowires. Nano Research, 2010, 3, 528-536.	5.8	161
143	Statistical analysis of excitonic transitions in single, free-standing GaN nanowires: Probing impurity incorporation in the poissonian limit. Nano Research, 2010, 3, 881-888.	5.8	24
144	High defect concentration in GaN:Gd layers grown by reactive molecular beam epitaxy. Solid State Communications, 2010, 150, 2370-2373.	0.9	14

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145	Rate-equation model of spin dynamics and polarized light emission for spin light-emitting diodes. Physical Review B, 2010, 81, .	1.1	6
146	Carrier capture by threading dislocations in (In,Ga)N/GaN heteroepitaxial layers. Physical Review B, 2010, 81, .	1.1	25
147	Unpinning the Fermi level of GaN nanowires by ultraviolet radiation. Physical Review B, 2010, 82, .	1.1	60
148	Reflection high-energy electron diffraction Ï• scans for in situ monitoring the heteroepitaxial growth of Fe on GaN(0001) by molecular beam epitaxy. Applied Physics Letters, 2010, 97, 031906.	1.5	16
149	â€œCube on hexagonâ€ orientation relationship for Fe on <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>GaN</mml:mtext><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mn>000</mml:mn>	1.1	15
150	The missing link in bcc/hcp epitaxy. Physical Review B, 2010, 82, . Single crystalline Sc2O3/Y2O3 heterostructures as novel engineered buffer approach for GaN integration on Si (111). Journal of Applied Physics, 2010, 108, 063502.	1.1	30
151	High-Temperature Ferromagnetism in the Super-Dilute Magnetic Semiconductor GaN:Gd. Topics in Applied Physics, 2010, , 309-342.	0.4	3
152	Collector Phase Transitions during Vaporâ^'Solidâ^'Solid Nucleation of GaN Nanowires. Nano Letters, 2010, 10, 3426-3431.	4.5	46
153	Sub-meV linewidth of excitonic luminescence in single GaN nanowires: Direct evidence for surface excitons. Physical Review B, 2010, 81, .	1.1	104
154	Advances in Group-III-Nitride Photodetectors. Open Electrical and Electronic Engineering Journal, 2010, 4, 1-9.	0.6	14
155	Thermal stability of epitaxial Fe films on GaN(0001). Applied Physics Letters, 2009, 95, 111906.	1.5	25
156	X-ray diffraction of epitaxial films with arbitrarily correlated dislocations: Monte Carlo calculation and experiment. Physical Review B, 2009, 80, .	1.1	27
157	Narrowâ€band photodetection based on M â€plane GaN films. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1100-1102.	0.8	7
158	Optically induced strain relaxation in anisotropically strainedM -plane GaN films. Physica Status Solidi (B): Basic Research, 2008, 245, 913-915.	0.7	4
159	Optically induced relaxation of anisotropically strained M-plane GaN films on LiAlO2. Journal of Applied Physics, 2008, 104, 063507.	1.1	4
160	Growth of M-plane MnAs on GaAs(111)B by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 101918.	1.5	5
161	Epitaxial orientation of MnAs layers grown on GaAs surfaces by means of solid-state crystallization. Physical Review B, 2008, 78, .	1.1	9
162	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Co</mml:mtext></mml:mrow><mml:mn>2</mml:mn> light-emitting diodes: Competition between spin injecti. Physical Review B, 2008, 78, .	1.1	84

#	Article	IF	Citations
163	Long-time evolution of the photoluminescence in C- and M-plane GaNâˆ•AlN quantum dots upon intense ultraviolet irradiation. Applied Physics Letters, 2008, 93, 081907.	1.5	6
164	Impact of carrier localization on the photoluminescence characteristics of (Ga,In)(N,As) and (Ga,In)(N,As,Sb) quantum wells. Journal of Applied Physics, 2008, 104, .	1.1	15
165	(Al,In)N layers and (Al,In)N/GaN heterostructures grown by plasma-assisted molecular beam epitaxy on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>6</mml:mn><mml:mi>H</mml:mi><mml:mtext>-SiC</mml:mtext><mml:mrow><mml:mo>(Physical Review B, 2008, 78, .	1.1	20
166	Structural, optical, and magnetic properties of (Ga,Mn)Asâˆ•AlAs multiple quantum well structures. Journal of Vacuum Science & Technology B, 2007, 25, 1460.	1.3	0
167	Strained M-plane GaN for polarization-sensitive applications. , 2007, , .		0
168	Exciton impact-ionization dynamics modulated by surface acoustic waves in GaN. Physical Review B, 2007, 75, .	1.1	16
169	Detection of the optical polarization angle with bandpass characteristics based on M-plane GaN photodetectors. Applied Physics Letters, 2007, 91, 203514.	1.5	6
170	Complete in-plane polarization anisotropy of the A exciton in unstrained A-plane GaN films. Applied Physics Letters, 2007, 91, 141903.	1.5	29
171	Hole spin polarization inGaAs:Mnâˆ•AlAsmultiple quantum wells. Physical Review B, 2007, 75, .	1.1	15
172	Very narrow-band ultraviolet photodetection based on strained M-plane GaN films. Applied Physics Letters, 2007, 90, 091110.	1.5	30
173	Intrinsic photoluminescence of M-plane GaN films on LiAlO2 substrates. Journal of Applied Physics, 2007, 101, 053527.	1.1	14
174	Optical polarization properties of M-plane GaN films investigated by transmittance anisotropy spectroscopy. Applied Physics Letters, 2007, 91, 251913.	1.5	5
175	Polarization-dependent beam switch based on an M-plane GaNâˆ•AlN distributed Bragg reflector. Applied Physics Letters, 2007, 90, 231117.	1.5	17
176	Epitaxial growth of 6H-AlN on M-plane SiC by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2007, 300, 127-129.	0.7	14
177	Fast time behavior of the polarization filtering in anisotropically strainedM -plane GaN films. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 175-178.	0.8	1
178	M -plane GaN-based dichroic photodetectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 86-89.	0.8	6
179	Electrical and optical characterization ofM-plane GaN films grown on LiAlO2 substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2548-2551.	0.8	3
180	Hot-Electron Photoluminescence of Para- and Ferromagnetic (Ga,Mn)As Layers. AIP Conference Proceedings, 2007, , .	0.3	1

#	Article	IF	Citations
181	Polarization-sensitive ultraviolet photodetectors based on M-plane GaN grown on LiAlO2 substrates. Applied Physics Letters, 2006, 88, 213507.	1.5	52
182	Formation of planar defects during the initial growth ofM-plane GaN on LiAlO2(100). European Physical Journal Special Topics, 2006, 132, 221-224.	0.2	8
183	Dynamic polarization rotation in pump-and-probe transients of anisotropically strainedM -plane GaN films on LiAlO2. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1862-1865.	0.8	0
184	Photocapacitance characteristics of (In,Ga)N/GaN MQW structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1978-1982.	0.8	2
185	The benefit of disorder. Nature Materials, 2006, 5, 769-770.	13.3	43
186	Ultrafast behavior of the polarization filtering in anisotropically strainedM-plane GaN films: A time-resolved pump-probe spectroscopy study. Physical Review B, 2006, 74, .	1.1	11
187	Hot-electron photoluminescence study of the(Ga,Mn)Asdiluted magnetic semiconductor. Physical Review B, 2006, 73, .	1.1	29
188	Magnetic phases and anisotropy in Gd-dopedGaN. Physical Review B, 2006, 74, .	1.1	40
189	Polarization anisotropy in GaN films for different nonpolar orientations studied by polarized photoreflectance spectroscopy. Applied Physics Letters, 2006, 88, 161920.	1.5	51
190	Influence of localization on the carrier diffusion inGaAsâˆ•(Al,Ga)Asand(In,Ga)(As,N)âˆ•GaAsquantum wells: A comparative study. Physical Review B, 2006, 73, .	1.1	16
191	Conductive and crack-free AlN/GaN:Si distributed Bragg reflectors grown on 6H-SiC(0001). Journal of Crystal Growth, 2005, 278, 355-360.	0.7	8
192	Polarization anisotropy and filtering forM-plane GaN films. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2704-2707.	0.8	2
193	Controlled n-type doping of AlN:Si films grown on 6H-SiC(0001) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2005, 86, 024106.	1.5	70
194	Ferrimagnetic Mn4N(111) layers grown on 6H-SiC(0001) and GaN(0001) by reactive molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 112504.	1.5	35
195	Dynamic polarization filtering in anisotropically strained M-plane GaN films. Applied Physics Letters, 2005, 86, 191909.	1.5	15
196	Combined hydride and metal organic vapor-phase epitaxy of GaN on sapphire. Applied Physics Letters, 2005, 87, 181912.	1.5	6
197	Gd-doped GaN: A very dilute ferromagnetic semiconductor with a Curie temperature above 300 K. Physical Review B, 2005, 72, .	1.1	132
198	X-ray diffraction peak profiles from threading dislocations in GaN epitaxial films. Physical Review B, 2005, 72, .	1.1	179

#	Article	IF	Citations
199	Colossal Magnetic Moment of Gd in GaN. Physical Review Letters, 2005, 94, 037205.	2.9	338
200	Surface-acoustic-wave transducers for the extremely-high-frequency range using AlN/SiC(0001). Semiconductor Science and Technology, 2004, 19, 256-259.	1.0	24
201	Strain relaxation in AlN/GaN bilayer films grown on Î³-LiAlO2(100) for nanoelectromechanical systems. Applied Physics Letters, 2004, 84, 4756-4758.	1.5	12
202	Crack-free and conductive Si-doped AlNâˆ•GaN distributed Bragg reflectors grown on 6H-SiC(0001). Applied Physics Letters, 2004, 85, 1970-1972.	1.5	46
203	Polarization filtering by nonpolar M-plane GaN films on LiAlO2. Journal of Applied Physics, 2004, 96, 7029-7035.	1.1	27
204	Growth of Nonpolar (1100) Films and Heterostructures by Plasma-Assisted Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2004, 831, 311.	0.1	1
205	Microstructure of M-plane GaN epilayers grown on Î³-LiAlO2 by plasma-assisted molecular beam epitaxy. Philosophical Magazine Letters, 2004, 84, 435-441.	0.5	44
206	Growth of M-plane GaN on Î³-: the role of Ga adsorption/desorption. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 23, 339-346.	1.3	13
207	Properties of InN layers grown on 6Hâ€“SiC(0001) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2004, 84, 1671-1673.	1.5	49
208	Highly anisotropic dispersion of surface acoustic waves in M-plane GaN layers grown onÎ³â^'LiAlO2(100). Physical Review B, 2004, 69, .	1.1	9
209	Ga adsorption and desorption kinetics onM-plane GaN. Physical Review B, 2004, 69, .	1.1	49
210	Impact of exciton localization on the optical properties of non-polarM-plane In0.1Ga0.9N/GaN multiple quantum wells. Physica Status Solidi (B): Basic Research, 2003, 240, 360-363.	0.7	2
211	Angular dependence of the in-plane polarization anisotropy in the absorption coefficient of strainedM-plane GaN films onÎ³-LiAlO2. Physica Status Solidi (B): Basic Research, 2003, 240, 293-296.	0.7	1
212	Polarization anisotropy of the photoluminescence of M-plane (In,Ga)N/GaN multiple quantum wells. Applied Physics Letters, 2003, 82, 3850-3852.	1.5	92
213	In situoptical reflectometry applied to growth of indium gallium nitride epilayers and multi-quantum well structures. Semiconductor Science and Technology, 2003, 18, 212-218.	1.0	42
214	Exciton localization and quantum efficiencyâ€”A comparative cathodoluminescence study of (In,Ga)N/GaN and GaN/(Al,Ga)N quantum wells. Journal of Applied Physics, 2003, 93, 1048-1053.	1.1	18
215	Photoluminescence intensity of GaN films with widely varying dislocation density. Journal of Materials Research, 2003, 18, 1247-1250.	1.2	11
216	Observation of spin-glass behavior in homogeneous (Ga,Mn)N layers grown by reactive molecular-beam epitaxy. Physical Review B, 2003, 67, .	1.1	110

#	Article	IF	Citations
217	Improved synthesis of (In,Ga)N/GaN multiple quantum wells by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2003, 83, 90-92.	1.5	9
218	Relation between photoreflectance excitation and absorption spectra for GaAs and GaN films. Journal of Applied Physics, 2003, 93, 221-225.	1.1	6
219	NonpolarInxGa1â^'xN/GaN(11Â¯00)multiple quantum wells grown onÎ³â^'LiAlO2(100)by plasma-assisted molecular-beam epitaxy. Physical Review B, 2003, 67, .	1.1	91
220	In surface segregation in M-plane (In,Ga)N/GaN multiple quantum well structures. Applied Physics Letters, 2003, 83, 5178-5180.	1.5	21
221	Origin of high-temperature ferromagnetism in (Ga,Mn)N layers grown on 4Hâ€“SiC(0001) by reactive molecular-beam epitaxy. Applied Physics Letters, 2003, 82, 2077-2079.	1.5	197
222	In-plane polarization anisotropy and polarization rotation for M-plane GaN films on LiAlO2. Applied Physics Letters, 2003, 83, 4327-4329.	1.5	17
223	Growth of M-plane GaN films on Î³-LiAlO[sub 2](100) with high phase purity. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1350.	1.6	60
224	Surface-Acoustic-Wave Delay Line at 24 GHz Using the Guided Rayleigh Mode in AlN/SiC Structures. Japanese Journal of Applied Physics, 2003, 42, 1594-1595.	0.8	10
225	Structural properties of InxGa1ÂxN/GaN and AlxGa1ÂxN/GaN MQWs studied by XRD. Journal Physics D: Applied Physics, 2003, 36, A192-A197.	1.3	6
226	Strained M-plane GaN for the realization of polarization-sensitive photodetectors. Applied Physics Letters, 2002, 81, 3380-3382.	1.5	40
227	Guided propagation of surface acoustic waves in AlN and GaN films grown on4Hâ€“SiC(0001)substrates. Physical Review B, 2002, 66, .	1.1	53
228	Superhigh-frequency surface-acoustic-wave transducers using AlN layers grown on SiC substrates. Applied Physics Letters, 2002, 81, 2538-2540.	1.5	76
229	Properties of (In,Ga)N/GaN quantum wells grown by plasma-assisted molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1626.	1.6	11
230	Polarization-dependent spectroscopic study of M-plane GaN on Î³-LiAlO2. Applied Physics Letters, 2002, 80, 413-415.	1.5	53
231	Influence of exciton localization on the quantum efficiency of GaN/(In,Ga)N multiple quantum wells grown by molecular-beam epitaxy. Applied Physics Letters, 2002, 81, 673-675.	1.5	19
232	In surface segregation during growth of (In,Ga)N/GaN multiple quantum wells by plasma-assisted molecular beam epitaxy. Physical Review B, 2002, 66, .	1.1	23
233	Strain field and chemical composition determination of InGaN/GaN and AlGaN/GaN multiple quantum wells grown on SiC substrates. Journal of Applied Physics, 2002, 92, 70-76.	1.1	9
234	Determination of strain state and composition of highly mismatched group-III nitride heterostructures by x-ray diffraction. Journal Physics D: Applied Physics, 2002, 35, 577-585.	1.3	89

#	Article	IF	Citations
235	Impact of nucleation conditions on the structural and optical properties ofM-plane GaN(11Ì„00) grown on Î³-LiAlO2. Journal of Applied Physics, 2002, 92, 5714-5719.	1.1	143
236	Determination of the azimuthal orientational spread of GaN films by x-ray diffraction. Applied Physics Letters, 2002, 81, 4928-4930.	1.5	73
237	Electronic band structure of wurtzite GaN under biaxial strain in theMplane investigated with photoreflectance spectroscopy. Physical Review B, 2002, 65, .	1.1	236
238	Electronic Band Structure of Strained C- and M-Plane GaN Films Investigated by Polarized Photoreflectance Spectroscopy. Physica Status Solidi (B): Basic Research, 2002, 234, 882-886.	0.7	4
239	Line Shape Analysis of Photoreflectance Excitation Spectra of GaN Films on 6H-SiC(0001). Physica Status Solidi A, 2002, 192, 144-150.	1.7	1
240	Impact of In Bulk and Surface Segregation on the Optical Properties of (In,Ga)N/GaN Multiple Quantum Wells. Physica Status Solidi A, 2002, 192, 5-13.	1.7	8
241	Comparative Study of the Electronic Band Structure of StrainedC-plane andM-plane GaN Films by Polarized Photoreflectance Spectroscopy. Physica Status Solidi A, 2002, 192, 72-78.	1.7	2
242	Indentation of GaN: A Study of the Optical Activity and Strain State of Extended Defects. Physica Status Solidi A, 2002, 192, 79-84.	1.7	24
243	Effect of Exciton Localization on the Quantum Efficiency of GaN/(In,Ga)N Multiple Quantum Wells. Physica Status Solidi A, 2002, 192, 85-90.	1.7	11
244	Anharmonicity of the E2(high) and A1(LO) phonons in GaN studied by temperature-dependent Raman spectroscopy. Physica B: Condensed Matter, 2002, 316-317, 162-165.	1.3	3
245	Cathodoluminescence of GaAs/(Al,Ga)As and (In,Ga)N/GaN heterostructures grown by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 329-335.	1.7	2
246	Influence of heteroepitaxy on the width and frequency of the E2 (high)-phonon line in GaN studied by Raman spectroscopy. Journal of Applied Physics, 2001, 89, 3634-3641.	1.1	27
247	Comparative study of the spontaneous and stimulated emission of M- and C-plane GaN/(Al,Ga)N quantum wells. , 2001, 4283, 96.		0
248	Indium Surface Segregation during Growth of (In,Ga)N/GaN Multiple Quantum Wells by Plasma-Assisted Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2001, 228, 49-53.	0.7	15
249	Impact of Internal Electric Field and Localization Effect on Quantum Well Excitons in AlGaN/GaN/InGaN Light Emitting Diodes. Physica Status Solidi A, 2001, 183, 91-98.	1.7	70
250	M-plane GaN grown on Î³-LiAlO2(100): nitride semiconductors free of internal electrostatic fields. Journal of Crystal Growth, 2001, 227-228, 437-441.	0.7	35
251	Key issues for the growth of high quality (Al,Ga)N/GaN and GaN/(In,Ga)N heterostructures on SiC(0 0 0) Tj ETQq1 1 0.784314 rgBT /O	3.1	8
252	Optical properties of wurtziteAlxGa1â^'xN(x<0.1) parallel and perpendicular to thecaxis. Physical Review B, 2001, 64, .	1.1	24

#	Article	IF	Citations
253	Electrostatic fields and compositional fluctuations in (In,Ga)N/GaN multiple quantum wells grown by plasma-assisted molecular-beam epitaxy. Physical Review B, 2001, 64, .	1.1	23
254	Optimization of the signal-to-noise ratio for photoreflectance spectroscopy. Journal of Applied Physics, 2001, 90, 5081-5085.	1.1	7
255	Growth of M-Plane GaN(11-00): A Way to Evade Electrical Polarization in Nitrides. Physica Status Solidi A, 2000, 180, 133-138.	1.7	64
256	Effective Localization of Quantum Well Excitons in InGaN Quantum Well Structures with High InN Mole Fraction. Physica Status Solidi A, 2000, 180, 321-325.	1.7	1
257	Temperature Dependence of the Photoreflectance Lineshape for GaN Films Grown by Molecular Beam Epitaxy. Physica Status Solidi A, 2000, 180, 381-386.	1.7	4
258	Morphology of GaN Surfaces and GaN/(Al,Ga)N Interfaces Grown on 6H-SiC(0001) by Reactive Molecular Beam Epitaxy. Physica Status Solidi A, 2000, 180, 73-79.	1.7	7
259	Growth of M-plane GaN(100) on Î³-LiAlO. Journal of Crystal Growth, 2000, 218, 143-147.	0.7	131
260	Nitride semiconductors free of electrostatic fields for efficient white light-emitting diodes. Nature, 2000, 406, 865-868.	13.7	1,662
261	Growth of high-quality (Al,Ga)N and (Ga,In)N heterostructures on SiC(0001) by both plasma-assisted and reactive molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2290.	1.6	24
262	Unpinned behavior of the surface Fermi level of GaN detected by photoreflectance spectroscopy. Journal of Applied Physics, 2000, 87, 4315-4318.	1.1	31
263	In-plane polarization anisotropy of the spontaneous emission of M-plane GaN/(Al,Ga)N quantum wells. Applied Physics Letters, 2000, 77, 3343-3345.	1.5	85
264	Optical properties of heavily dopedGaN/(Al,Ga)Nmultiple quantum wells grown on6Hâ^'SiC(0001)by reactive molecular-beam epitaxy. Physical Review B, 2000, 61, 16025-16028.	1.1	19
265	Evidence of localization effects in InGaN single-quantum-well ultraviolet light-emitting diodes. Applied Physics Letters, 2000, 76, 1671-1673.	1.5	52
266	Critical issues for the growth of high-quality (Al,Ga)N/GaN and GaN/(In,Ga)N heterostructures on SiC(0001) by molecular-beam epitaxy. Applied Physics Letters, 1999, 75, 4019-4021.	1.5	88
267	Violet and blue emitting (In,Ga)N/GaN multiple quantum wells grown on Î³-LiAlO2(100) by radio frequency plasma-assisted molecular beam epitaxy. Applied Physics Letters, 1999, 75, 2029-2031.	1.5	27
268	Reactive molecular-beam epitaxy of GaN layers directly on 6Hâ€“SiC(0001). Applied Physics Letters, 1999, 75, 944-946.	1.5	44
269	Patterning of cubic and hexagonal GaN by Cl2/N2-based reactive ion etching. Applied Physics Letters, 1999, 74, 3471-3473.	1.5	8
270	Properties of cubic (In,Ga)N grown by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 73-79.	1.7	20

#	Article	IF	Citations
271	Structural properties of GaN epilayers directly grown on on-axis 6H-SiC(0001) by plasma-assisted MBE. Journal of Crystal Growth, 1999, 201-202, 407-410.	0.7	8
272	High Pressure Luminescence of Zincblende and Wurtzite GaN. Physica Status Solidi (B): Basic Research, 1999, 211, 57-61.	0.7	11
273	Influence of Internal Polarization Fields on the Disorder Broadening of Excitons in (In,Ga)N/GaN Quantum Wells. Physica Status Solidi (B): Basic Research, 1999, 216, 419-422.	0.7	1
274	Influence of AlN nucleation layers on growth mode and strain relief of GaN grown on 6Hâ€“SiC(0001). Applied Physics Letters, 1999, 74, 3660-3662.	1.5	113
275	Recombination dynamics in GaN. Journal of Crystal Growth, 1998, 189-190, 790-793.	0.7	40
276	Growth and mosaic model of GaN grown directly on 6Hâ€“SiC(0001) by direct current plasma assisted molecular beam epitaxy. Journal of Crystal Growth, 1998, 192, 28-32.	0.7	28
277	Ga-terminated Î²-GaN(001) surface reconstructions studied by scanning tunneling microscopy. Applied Surface Science, 1998, 123-124, 181-186.	3.1	5
278	Optical properties of cubic GaN and (In,Ga)N. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 532-538.	1.3	12
279	Growth of cubic GaN on Si(001) by plasma-assisted MBE. Applied Surface Science, 1998, 123-124, 1-6.	3.1	19
280	Doping of group III nitrides. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 1609-1614.	0.9	63
281	Green photoluminescence from cubic In0.4Ga0.6N grown by radio frequency plasma-assisted molecular beam epitaxy. Applied Physics Letters, 1998, 73, 1230-1232.	1.5	21
282	Temperature dependence of the radiative lifetime in GaN. Physical Review B, 1998, 58, R15977-R15980.	1.1	83
283	Structural and Optical Properties of GaN Layers Directly Grown on 6H-SiC(0001) by Plasma-Assisted Molecular Beam Epitaxy. Materials Science Forum, 1998, 264-268, 1235-1238.	0.3	2
284	Long-wavelength (Ga, In)Sb/GaSb strained quantum well lasers grown by molecular beam epitaxy. Semiconductor Science and Technology, 1998, 13, 936-940.	1.0	22
285	Impact of exciton diffusion on the optical properties of thin GaN layers. Physical Review B, 1998, 58, R13407-R13410.	1.1	11
286	Interface electronic transition observed by optical second-harmonic spectroscopy inÎ²â˜GaN/GaAs(001)heterostructures. Physical Review B, 1998, 57, 3722-3725.	1.1	8
287	Nucleation and growth of GaN layers on GaAs, Si, and SiC substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2229.	1.6	33
288	Structural characterization of thin GaN epilayers directly grown on on-axis 6Hâ€“SiC(0001) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 1998, 73, 3869-3871.	1.5	22

#	Article	IF	Citations
289	Direct comparison of the pressure-induced band-gap shifts in cubic and hexagonal GaN. Journal of Applied Physics, 1998, 84, 2971-2973.	1.1	8
290	Structural properties of GaN layers on Si(001) grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 1998, 83, 3800-3806.	1.1	34
291	Overdamped excitations of the free electron gas in GaN layers studied by Raman spectroscopy. Physical Review B, 1998, 58, 1118-1121.	1.1	33
292	Are cubic nitrides viable materials for optoelectronic devices?. , 1998, 3279, 38.		1
293	Growth and doping of cubic GaN films for optoelectronic devices. , 1998, , .		2
294	Plasma-assisted molecular beam epitaxial growth and characterization of zincblende (In,Al,Ga)N heterostructures on GaAs(001). , 1998, , .		0
295	Response to â€œComment on â€˜Shallow donors in GaN studied by electronic Raman scattering in resonance with yellow luminescence transitionsâ€™â€‰â€•[Appl. Phys. Lett.70, 909 (1997)]. Applied Physics Letters, 1997, 70, 910-911.	1.5	7
296	Cubic (In,Ga)N layers grown on GaAs(001) by dc plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 1997, 82, 1918-1920.	1.1	30
297	Excitons in strained (Ga,In)Sb/GaSb quantum wells. Physical Review B, 1997, 55, 4503-4505.	1.1	6
298	Optimized growth conditions for the epitaxial nucleation of Î²-GaN on GaAs(001) by molecular beam epitaxy. Applied Physics Letters, 1997, 71, 473-475.	1.5	40
299	Direct observation of the initial nucleation and epitaxial growth of metastable cubic GaN on (001) GaAs. Applied Physics Letters, 1997, 70, 583-585.	1.5	78
300	Valence band discontinuity at a cubic GaN/GaAs heterojunction measured by synchrotron-radiation photoemission spectroscopy. Applied Physics Letters, 1997, 70, 2407-2409.	1.5	56
301	Time-resolved photoluminescence investigations of cubic GaN layers and crystals up to room temperature. Applied Physics Letters, 1997, 70, 1808-1810.	1.5	13
302	Electronic and vibrational Raman scattering in resonance with yellow luminescence transitions in GaN on sapphire substrate. , 1997, , .		0
303	Chapter 7 Crystal Structure of Group III Nitrides. Semiconductors and Semimetals, 1997, 50, 167-192.	0.4	28
304	Growth and doping of /spl beta/-GaN and /spl beta/-(In,Ga)N films and heterostructures. , 1997, , .		0
305	Characterization of zinc blende InxGa1âˆ’xN grown by radio frequency plasma assisted molecular beam epitaxy on GaAs (001). Applied Physics Letters, 1997, 71, 909-911.	1.5	21
306	Atomic structure of the surface reconstructions of zincblende GaN(001). Surface Science, 1997, 385, 178-186.	0.8	17

#	Article	IF	Citations
307	Optical gain in optically pumped cubic GaN at room temperature. Applied Physics Letters, 1997, 70, 1076-1077.	1.5	35
308	Relation between surface reconstruction transitions and growth kinetics of zincblende (0 0 1) GaN. Journal of Crystal Growth, 1997, 175-176, 134-138.	0.7	0
309	Properties of cubic GaN grown by MBE. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 43, 215-221.	1.7	18
310	MBE growth and characteristics of cubic GaN. Thin Solid Films, 1997, 306, 231-236.	0.8	12
311	Interplay between growth kinetics and material quality of cubic GaN. Solid-State Electronics, 1997, 41, 235-237.	0.8	17
312	Phase Transformations and Phase Stability in EpitaxialÎ²-GaN Films. Angewandte Chemie International Edition in English, 1997, 36, 2111-2112.	4.4	7
313	Heteroepitaxy of Cubic GaN. Journal De Physique III, 1997, 7, 2309-2316.	0.3	0
314	High pâ€type conductivity in cubic GaN/GaAs(113)A by using Be as the acceptor and O as the codopant. Applied Physics Letters, 1996, 69, 2707-2709.	1.5	135
315	Evaluation of the surface stoichiometry during molecular beam epitaxy of cubic GaN on (001) GaAs. Applied Physics Letters, 1996, 68, 244-246.	1.5	60
316	Identification of optical transitions in cubic and hexagonal GaN by spatially resolved cathodoluminescence. Physical Review B, 1996, 53, 1881-1885.	1.1	142
317	Shallow donors in GaN studied by electronic Raman scattering in resonance with yellow luminescence transitions. Applied Physics Letters, 1996, 69, 1276-1278.	1.5	55
318	Real-time monitoring of the surface stoichiometry during molecular beam epitaxy of cubic GaN on (001) GaAs by RHEED. Journal of Electronic Materials, 1996, 25, 787-791.	1.0	17
319	Kinematical RHEED simulation of different structure models for the GaAs (311)A surface. Applied Surface Science, 1996, 104-105, 35-44.	3.1	15
320	Initial stage of growth of in plasma-assisted molecular beam epitaxy. Applied Surface Science, 1996, 104-105, 461-467.	3.1	18
321	MBE growth of cubic GaN on GaAs substrates. Physica Status Solidi (B): Basic Research, 1996, 194, 109-120.	0.7	60
322	Impact of recombination centers on the spontaneous emission of semiconductors under steady-state and transient conditions. Physical Review B, 1996, 54, R5215-R5218.	1.1	48
323	Structural and optical properties of strained (Ga,In)Sb/GaSb quantum wells grown by molecularâ€beam epitaxy. Applied Physics Letters, 1996, 69, 2237-2239.	1.5	9
324	Optical transitions in cubic GaN investigated by spatially resolved cathodoluminescence. Applied Physics Letters, 1996, 69, 836-838.	1.5	28

#	Article	IF	Citations
325	Electronic structure of cubic gallium nitride films grown on GaAs. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 819-824.	0.9	47
326	Growth mode, strain relief, and segregation of (Ga,In)Sb on GaSb(001) grown by molecular beam epitaxy. Applied Physics Letters, 1996, 68, 31-33.	1.5	41
327	Surface kinetics of zinc-blende (001) GaN. Physical Review B, 1996, 54, 4432-4435.	1.1	59
328	Recombination Dynamics of Near-Bandedge Emission in Cubic GaN. , 1996, , 259-263.		2
329	Exciton Luminescence of Single-Crystal GaN. Materials Research Society Symposia Proceedings, 1995, 395, 607.	0.1	7
330	Does The 1.25 eV Luminescence of Coherently Strained InGaAs Insertions in GaAs Originate from Quantum Dots?. Materials Research Society Symposia Proceedings, 1995, 417, 199.	0.1	1
331	Growth of Cubic G<scp>A</scp>N on (001) G<scp>A</scp>AS. Materials Research Society Symposia Proceedings, 1995, 395, 27.	0.1	14
332	High pressure study of Î“-X mixing in InAs/GaAs quantum dots. Journal of Physics and Chemistry of Solids, 1995, 56, 385-388.	1.9	14
333	Optical anisotropy of (11N) and vicinal (001) quantum wells. Journal of Crystal Growth, 1995, 150, 431-435.	0.7	14
334	Coherently strained InAs insertions in GaAs: do they form quantum wires and dots?. Microelectronics Journal, 1995, 26, 861-870.	1.1	8
335	Optical phonons of hexagonal and cubic GaN studied by infrared transmission and Raman spectroscopy. Applied Physics Letters, 1995, 67, 733-735.	1.5	127
336	Recombination processes and photoluminescence intensity in quantum wells under steady-state and transient conditions. Physical Review B, 1995, 51, 7029-7037.	1.1	21
337	Surface reconstructions of zinc-blende GaN/GaAs(001) in plasma-assisted molecular-beam epitaxy. Physical Review B, 1995, 52, R2253-R2256.	1.1	159
338	Comparative analysis of the optical quality of single In0.1Ga0.9As/Al0.33Ga0.67As quantum wells grown by molecular beam epitaxy on (100) and (311) GaAs substrates. Applied Physics Letters, 1995, 67, 1885-1887.	1.5	12
339	Picosecond dynamics of excitons in cubic GaN. Physical Review B, 1995, 52, R11615-R11618.	1.1	30
340	State mixing in InAs/GaAs quantum dots at the pressure-induced Î“-Xcrossing. Physical Review B, 1994, 50, 18420-18425.	1.1	42
341	Effects of an electric field on exciton recombination in threeâ€step asymmetric coupled quantum wells. Journal of Applied Physics, 1994, 75, 2105-2109.	1.1	8
342	Photoluminescence from strained InAs monolayers in GaAs under pressure. Physical Review B, 1994, 50, 1575-1581.	1.1	49

#	Article	IF	Citations
343	Direct measurement of local lattice distortions in strained layer structures by HREM. Ultramicroscopy, 1993, 49, 273-285.	0.8	202
344	Gaussian line-shape analysis of the room temperature photoreflectance of GaAs/AlGaAs and InAs/GaAs multiple quantum wells. Solid State Communications, 1993, 87, 481-485.	0.9	9
345	Determination of the Sb composition profile in MBE-grown GaSb/GaAs structures by high-resolution X-ray diffractometry. Journal of Crystal Growth, 1993, 127, 503-507.	0.7	3
346	Effect of In segregation on the structural and optical properties of ultrathin InAs films in GaAs. Journal of Crystal Growth, 1993, 127, 513-514.	0.7	3
347	Structural and electronic properties of GaAs : C and AlxGa1-xAs : C grown by solid-source molecular beam epitaxy. Journal of Crystal Growth, 1993, 127, 724-727.	0.7	5
348	Virtual-surfactant epitaxy of InAs quantum wells. Journal of Crystal Growth, 1993, 127, 765-769.	0.7	17
349	Growth of [211]-oriented InAs/GaAs heterostructures. Journal of Crystal Growth, 1993, 127, 927-931.	0.7	1
350	Low-density band-filling in strained InAs quantum wells. Applied Physics A: Materials Science and Processing, 1993, 56, 109-112.	1.1	4
351	Virtual-surfactant-induced wetting in strained-layer heteroepitaxy. Applied Physics A: Solids and Surfaces, 1993, 56, 91-94.	1.4	15
352	Triple crystal xâ€ray diffractometry of periodic arrays of semiconductor quantum wires. Applied Physics Letters, 1993, 63, 3140-3142.	1.5	33
353	Determination of the lateral periodicity of nanometer quantum dot arrays by triple crystal diffractometry. Applied Physics Letters, 1993, 63, 156-158.	1.5	9
354	InAs monolayers and quantum dots in a crystalline GaAs matrix. Semiconductor Science and Technology, 1993, 8, S229-S235.	1.0	15
355	Optical properties of InAs quantum wells emitting between 0.9 mu m and 2.5 mu m. Semiconductor Science and Technology, 1993, 8, S236-S239.	1.0	9
356	Nucleation, Relaxation and Redistribution of Si Layers in GaAs. Japanese Journal of Applied Physics, 1993, 32, L24-L27.	0.8	13
357	Optical properties of a high-quality (311)-oriented GaAs/Al0.33Ga0.67As single quantum well. Physical Review B, 1993, 48, 17599-17602.	1.1	29
358	X-ray standing wave and high-resolution x-ray diffraction study of the GaAs/InAs/GaAs(100) heterointerface. Physical Review B, 1993, 48, 11496-11499.	1.1	54
359	Measurement of the Lateral Periodicity of a Quantum Dot Array by Triple Crystal Diffractometry. Materials Research Society Symposia Proceedings, 1993, 312, 119.	0.1	0
360	Breakdown of continuum elasticity theory in the limit of monatomic films. Physical Review Letters, 1992, 68, 1339-1342.	2.9	84

#	Article	IF	Citations
361	Molecular beam epitaxy of (211)â€InAs quantum sheets in GaAs. Applied Physics Letters, 1992, 61, 441-443.	1.5	9
362	Piezo-optical effects in GaAs with interspersed (211)-InAs lattice planes. Physical Review B, 1992, 45, 8825-8828.	1.1	14
363	Photoluminescence of virtualâ€surfactant grown InAs/Al0.48In0.52As single quantum wells. Applied Physics Letters, 1992, 60, 2877-2879.	1.5	43
364	Evidence for superradiant decay of excitons in InAs quantum sheets. Physical Review B, 1992, 45, 3803-3806.	1.1	27
365	Heavy- and light-hole character of optical transitions in InAs/GaAs single-monolayer quantum wells. Physical Review B, 1992, 45, 4217-4220.	1.1	45
366	Molecular-beam epitaxially grown Si/GaAs interfaces: Delta-doping, Si on GaAs, and GaAs on Si. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 841.	1.6	16
367	Formation and morphology of InAs/GaAs heterointerfaces. Physical Review B, 1992, 45, 8443-8453.	1.1	60
368	Effect of In segregation on the structural and optical properties of ultrathin InAs films in GaAs. Applied Physics Letters, 1992, 61, 2814-2816.	1.5	31
369	Direct synthesis of InAs quantum dots in single-crystalline GaAs matrix by molecular beam epitaxy. Surface Science, 1992, 267, 204-208.	0.8	9
370	Role of broken translational invariance for the optical response of excitons in low-dimensional semiconductors. Surface Science, 1992, 267, 319-322.	0.8	9
371	Influence of strain on structural and vibrational properties of (InAs)m(GaAs)n strained superlattices grown by molecular beam epitaxy. Applied Surface Science, 1992, 56-58, 610-616.	3.1	1
372	Strain relief process at highly strained semiconductor heterointerfaces studied by high-resolution X-ray diffraction. Applied Surface Science, 1992, 56-58, 650-655.	3.1	11
373	X-ray diffraction study of corrugated semiconductor surfaces, quantum wires and quantum â˜es. Applied Surface Science, 1992, 60-61, 517-521.	3.1	25
374	Direct Fabrication of IIIâ€“V Semiconductor Quantum Dots and Quantum Wires by Molecular Beam Epitaxy. Springer Series in Solid-state Sciences, 1992, , 134-142.	0.3	3
375	Structural and vibrational properties of (InAs)m(GaAs)nstrained superlattices grown by molecular beam epitaxy. Journal of Applied Physics, 1991, 69, 786-792.	1.1	20
376	InAs quantum dots in a single-crystal GaAs matrix. Physical Review B, 1991, 44, 8043-8053.	1.1	102
377	Spectroscopy study of monolayer InAs/GaAs single and multiple quantum wells grown by molecular beam epitaxy. Superlattices and Microstructures, 1991, 9, 147-150.	1.4	7
378	Synthesis and structural configuration of highly strained InAs films in GaAs. Journal of Crystal Growth, 1991, 115, 99-105.	0.7	6

#	Article	IF	Citations
379	Growth processes and relaxation mechanisms in the molecular beam epitaxy of InAs/GaAs heterostructures. Journal of Crystal Growth, 1991, 111, 383-387.	0.7	24
380	Excitons in InAs/GaAs submonolayer quantum wells. Physical Review B, 1991, 43, 14285-14288.	1.1	21
381	Redistribution of epitaxial Si on (001) GaAs during overgrowth by GaAs. Applied Physics Letters, 1991, 59, 2730-2732.	1.5	21
382	Large excitonic nonlinearity in InAs quantum sheets. Applied Physics Letters, 1991, 59, 576-578.	1.5	5
383	Mg incorporation process during LP-MOVPE of InP, GaInAs and GaInAsP. Journal of Crystal Growth, 1990, 105, 353-358.	0.7	12
384	Exciton localization in submonolayer InAs/GaAs multiple quantum wells. Physical Review B, 1990, 42, 3209-3212.	1.1	78
385	Radiative decay of excitonic states in bulklike GaAs with a periodic array of InAs lattice planes. Physical Review B, 1990, 42, 11396-11399.	1.1	17
386	Structural and optical properties of (100) InAs single-monolayer quantum wells in bulklike GaAs grown by molecular-beam epitaxy. Physical Review B, 1990, 41, 12599-12606.	1.1	119
387	Mg diffusion during metalorganic vapor phase epitaxy of InP. Applied Physics Letters, 1989, 55, 1017-1019.	1.5	24
388	Fabrication of device-related GaN/(Al,Ga)N heterostructures on SiC(0001) by reactive MBE. , 0, , .		2